Atomistic observation of defects evolution during solidification in Semiconductor InAs

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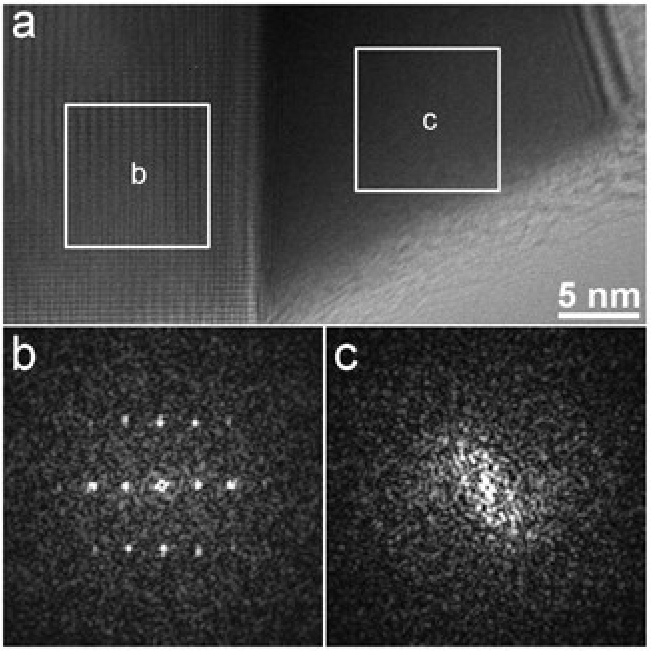

Figure S1. (a) A typical HRTEM image of the InAs with melted liquid. (b-c) Fast Fourier transform (FFT) images of InAs and liquid (white-boxed areas in (a)), respectively.